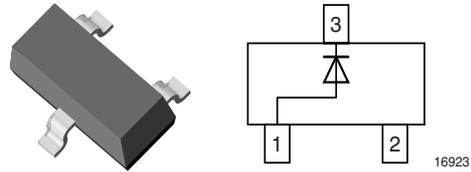


Small Signal Switching Diode

Features

- Silicon Epitaxial Planar Diodes
- Fast switching diode in case SOT-23, especially suited for automatic insertion.
- These diodes are also available in other case styles including: the DO-35 case with the type designation 1N4448, the Mini-MELF case with the type designation LL4448, and the SOD-123 case with the type designation 1N4448W.



Mechanical Data

Case: SOT-23 Plastic case

Weight: approx. 8.8 mg

Packaging Codes/Options:

GS18 / 10 k per 13" reel (8 mm tape), 10 k/box

GS08 / 3 k per 7" reel (8 mm tape), 15 k/box

Parts Table

Part	Ordering code	Marking	Remarks
IMBD4448	IMBD4448-GS18 or IMBD4448-GS08	A3	Tape and Reel

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	75	V
Peak reverse voltage		V_{RM}	100	V
Rectified current (average) half wave rectification with resist.	$T_{amb} = 25\text{ }^{\circ}\text{C}$ and $f \geq 50\text{ Hz}$	$I_{F(AV)}$	150 ¹⁾	mA
Surge forward current	$t < 1\text{ s}$ and $T_j = 25\text{ }^{\circ}\text{C}$	I_{FSM}	500	mA
Power dissipation	$T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	350 ¹⁾	mW

¹⁾ Device on fiberglass substrate, see layout (SOT-23).

Thermal Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air		R_{thJA}	450 ¹⁾	$^{\circ}\text{C/W}$
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature range		T_S	- 65 to + 150	$^{\circ}\text{C}$

¹⁾ Device on fiberglass substrate, see layout (SOT-23).

Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

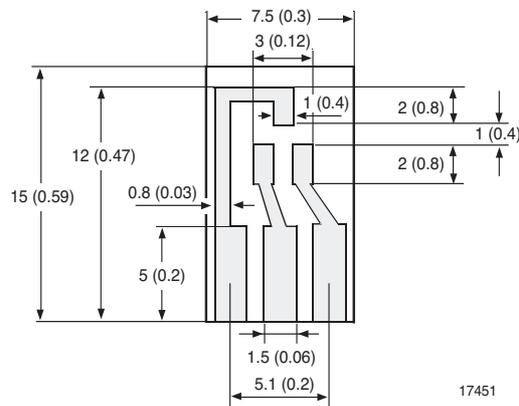
Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 5\text{ mA}$	V_F	0.62		0.72	V
	$I_F = 100\text{ mA}$	V_F			1.0	V
Leakage current	$V_R = 70\text{ V}$	I_R			2.5	μA
	$V_R = 70\text{ V}, T_j = 150\text{ }^{\circ}\text{C}$	I_R			50	μA
	$V_R = 25\text{ V}, T_j = 150\text{ }^{\circ}\text{C}$	I_R			30	μA
Diode capacitance	$V_F = V_R = 0$	C_{tot}			4	pF
Reverse recovery time (see figures)	$I_F = 10\text{ mA}, I_R = 10\text{ mA},$ $V_R = 6\text{ V}, R_L = 100\text{ }\Omega$	t_{rr}			4	ns

Layout for R_{thJA} test

Thickness:

Fiberglass 1.5 mm (0.059 in.)

Copper leads 0.3 mm (0.012 in.)



Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

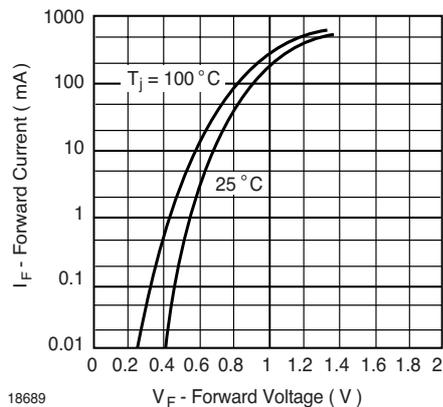


Figure 1. Forward Current vs. Forward Voltage

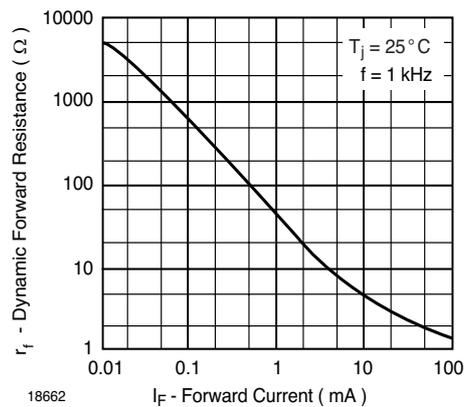


Figure 2. Dynamic Forward Resistance vs. Forward Current

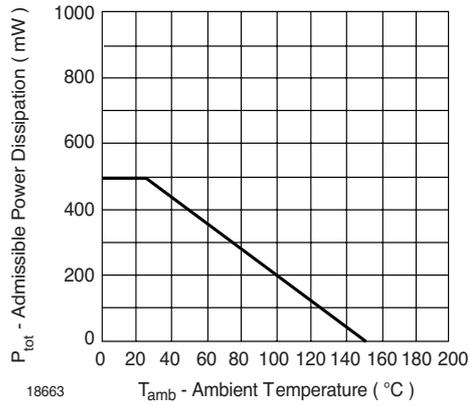


Figure 3. Admissible Power Dissipation vs. Ambient Temperature

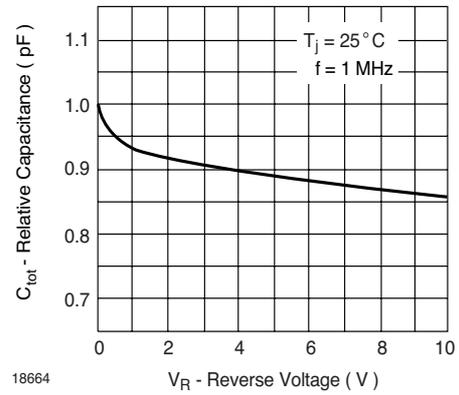


Figure 4. Relative Capacitance vs. Reverse Voltage

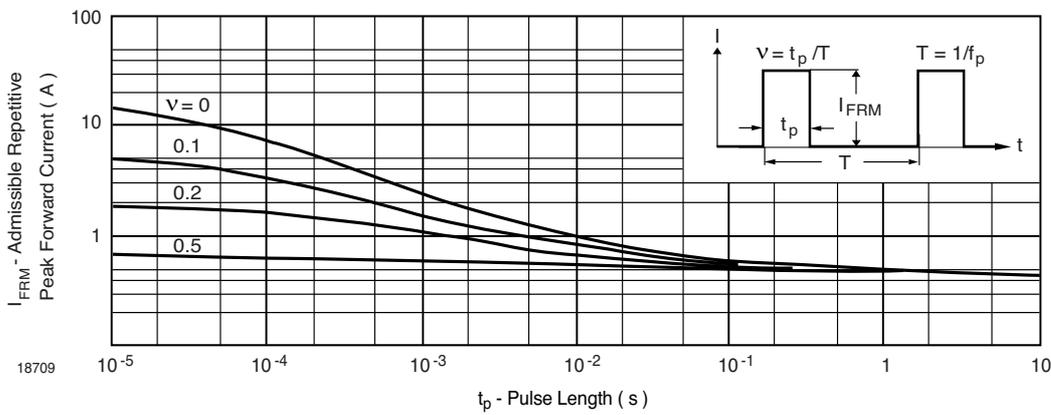
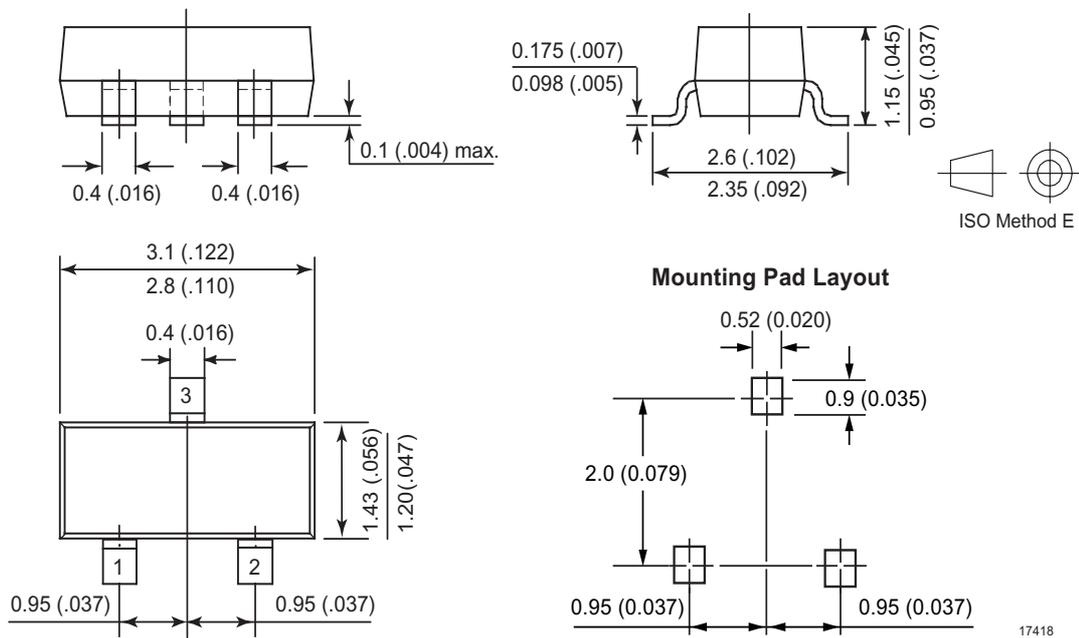


Figure 5. Admissible Repetitive Peak Forward Current vs. Pulse Duration

Package Dimensions in mm (Inches)



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design
and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany
Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423